Preliminary
RF2640

## Typical Applications

- TDMA/AMPS Cellular Systems

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- Portable Battery Powered Equipment
}
- CDMA/AMPS Cellular Systems


## Product Description

The RF2640 is a complete upconverter and power amplifier driver designed for TDMA and CDMA applications. The device features balanced IF inputs, single-ended LO input and RF output for ease of interface. Packaged in an industry standard MSOP-10 package, the device provides a low-cost solution while easing board space limitations.

Optimum Technology Matching ${ }^{\circledR}$ Applied

| $\square$ Si BJT | $\square$ GaAs HBT | $\square$ GaAs MESFET |
| :--- | :--- | :--- |
| $\square$ Si Bi-CMOS | $\square$ SiGe HBT | $\square$ Si CMOS |



Functional Block Diagram


Package Style: MSOP-10

## Features

- Single Supply 3.0V Operation
- +8.5 dBm Output P1dB
- +19dBm Output IP3
- Power Down Control
- 23dB Conversion Gain


## Ordering Information

RF2640 3V 900MHz Upconverter/ Driver Amplifier RF2640 PCBA Fully Assembled Evaluation Board

Absolute Maximum Ratings

| Parameter | Rating | Unit |
| :--- | :---: | :---: |
| Supply Voltage | -0.5 to +3.6 | $\mathrm{~V}_{\mathrm{DC}}$ |
| Input RF Power | +3 | $\mathrm{dBm}^{\circ} \mathrm{Co}$ |
| Operating Ambient Temperature | -30 to +80 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature | -30 to +150 | ${ }^{\circ} \mathrm{C}$ |



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| Parameter | Specification |  |  | Unit | Condition |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min. | Typ. | Max. |  |  |
| Overall |  |  |  |  | $\mathrm{T}=25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{CC}}=2.7 \mathrm{~V}, \mathrm{RF}$ Out $=836 \mathrm{MHz}$, LO $=1016 \mathrm{MHz} @-8 \mathrm{dBm}, \mathrm{IF}=180 \mathrm{MHz}$ @ -30dBm |
| RF Output Frequency Range | 824 |  | 849 | MHz |  |
| Conversion Gain | 22 | 23.5 | 26 | dB |  |
| Noise Figure |  | 12 |  | dB | Single Sideband |
| Output P1dB |  | +8.5 |  | dBm |  |
| Output IP3 | +17 | +18.5 |  | dBm |  |
| Output VSWR |  | 1.25:1 |  |  | $50 \Omega$ |
| IF Input |  |  |  |  |  |
| IF Frequency |  | 180 |  | MHz |  |
| IF Input Level | -60 |  | -15 | dBm |  |
| Single-Ended Input Impedance |  | 70 |  | $\Omega$ |  |
| IF to RF Isolation |  | 45 |  | dB |  |
| LO Input |  |  |  |  |  |
| LO Frequency Range | 1004 |  | 1029 | MHz |  |
| LO Level | -10 | -8 | -6 | dBm |  |
| LO to RF Output Leakage |  |  | -18 | dBm | IF Input<-24dBm |
| LO Input VSWR |  | 1.25:1 |  |  | $50 \Omega$ |
| Power Supply |  |  |  |  |  |
| Voltage | 2.7 | 45 | 3.3 | V |  |
| Current Consumption |  |  | 65 | mA | Device is active ( ON ) ; $\mathrm{V}_{\mathrm{PD}}=1.8 \mathrm{~V}$ |
|  |  |  | 10 | $\mu \mathrm{A}$ | Device is inactive (OFF); $\mathrm{V}_{\mathrm{PD}}=0.6 \mathrm{~V}$ |
| Power Down Voltage | 0.0 |  | 0.6 | V | Device is inactive (OFF); $\mathrm{V}_{\mathrm{PD}}=0.6 \mathrm{~V}$ |
|  | 1.2 |  | 1.8 | V | Device is active ( ON ); $\mathrm{V}_{\mathrm{PD}}=1.8 \mathrm{~V}$ |
| Power Down Current |  |  | 0.1 | mA | Device is active ( ON ); $\mathrm{V}_{\mathrm{PD}}=1.8 \mathrm{~V}$ |


| Pin | Function | Description | Interface Schematic |
| :---: | :---: | :---: | :---: |
| 1 | IF+ | Balanced IF input pin. This pin is internally DC-biased and should be DC-blocked if connected to a device with a DC level present. For singleended input operation, one pin is used as an input and the other IF input is AC-coupled to ground. The single-ended input impedance is $50 \Omega$. |  |
| 2 | IF- | Same as pin 1, except complementary input. |  |
| 3 | GND1 | Ground connection. For best performance, keep traces physically short and connect immediately to ground plane. |  |
| 4 | LO+ | Single-ended LO input pin. This pin is internally DC-biased and should be DC-blocked if connected to a device with a DC level present. The single-ended input impedance is $50 \Omega$. |  |
| 5 | GND2 | Same as pin 3, except complementary input. |  |
| 6 | RF OUT | RF Output Pin. The output impedance is $50 \Omega$. |  |
| 7 | RF GND | This pin requires a small inductance to ground to optimize the gain and third order intercept point. See Evaluation Board Layout. The trace length on the board is approximately 65 mils. |  |
| 8 | GND3 | Same as pin 7. |  |
| 9 | PD | Power down control. When logic "high" (between 1.2 V and 1.8 V ) the device is active and all circuits are operating. When logic "low" (between 0.0 V and 0.6 V ) the device is inactive and all circuits are turned off. |  |
| 10 | VCC | Supply Voltage pin. External bypassing is required. External RF, LO, and IF bypassing is required. The trace length between the pin and the bypass capacitors should be minimized. The ground side of the bypass capacitors should connect immediately to ground plane. |  |

## Evaluation Board Schematic

 $R F=836 \mathrm{MHz}, \mathrm{LO}=1016 \mathrm{MHz}$(Download Bill of Materials from www.rfmd.com.)


Evaluation Board Layout Board Size 2.0" x 2.0"<br>Board Thickness 0.031", Board Material FR-4




Evaluation Board 2640410(-)



OIP3 versus $\mathrm{V}_{\mathrm{cc}}$

$I_{c c}$ versus $V_{c c}$


Noise Figure versus $\mathrm{V}_{\mathrm{cc}}$


OP1dB versus $\mathrm{V}_{\mathrm{cc}}$ LO @ -8dBm




OIP3 versus LO $\mathrm{P}_{\text {IN }}$



